

## 2.7V to 5.5V, 2A 1ch Synchronous Buck Converter integrated FET

• Key Specification

#### **BD89630EFJ**

#### General Description

ROHM's high efficiency step-down switching regulator BD89630EFJ is a power supply designed to produce a low voltage including 1 volts from 5.5/3.3 volts power supply line. Offers high efficiency with synchronous rectifier. Employs a current mode control system to provide faster transient response to sudden change in load.

#### Features

- Offers fast transient response with current mode PWM control system.
- Offers highly efficiency for all load range with synchronous rectifier (Nch/Pch FET)
- Incorporates soft-start function.
- Incorporates thermal protection and ULVO functions.
- Incorporates short-current protection circuit with time delay function.
- Incorporates shutdown function

#### Applications

Power supply for LSI including DSP, Micro computer and ASIC

#### **●**Typical Application Circuit

# Input voltage range: 2.7V to 5.5V Output voltage range: 1.0V to 2.5V Average output Current: 2A(Max.) Switching frequency: 1MHz(Typ.) Pch FET ON resistance: 145m Ω (Typ.) Nch FET ON resistance: 80m Ω (Typ.)

Standby current: 5µA (Typ.)
 Operating temperature range: -25°C to +85°C

● Package (Typ.) (Typ.) (Max.) HTSOP-J8 4.90mm x 6.00mm x 1.00mm



HTSOP-J8

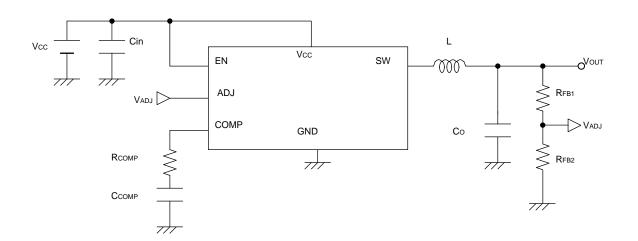


Fig.1 Typical Application Circuit

#### ●Pin configuration(TOP VIEW)

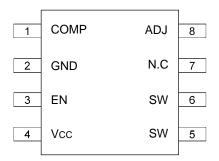


Fig.2 Pin configuration

#### Pin Description

Pin No.	Pin name	PIN function			
1	COMP	GmAmp output pin/Connected phase compensation capacitor			
2	GND	Ground			
3	EN	Enable pin(Active High, Open Active)			
4	Vcc	VCC power supply input pin			
5	SW	Pch/Nch FET drain output pin			
6	SW	Pch/Nch FET drain output pin			
7	N.C	Non Connect			
8	ADJ	Output voltage detect pin			

#### Block Diagram

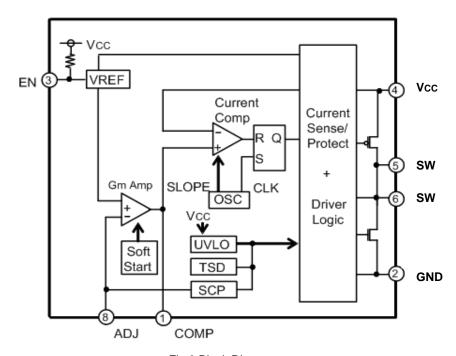


Fig.3 Block Diagram

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Vcc Voltage	Vcc	-0.3 to +7 *1	V
EN Voltage	VEN	-0.3 to +7	V
SW,COMP Voltage	Vsw,Vcomp	-0.3 to +7	V
Power Dissipation 1	Pd1	0.5 <sup>*2</sup>	W
Power Dissipation 2	Pd2	3.76 <sup>*3</sup>	W
Operating temperature range	Topr	-25 to +85	°C
Storage temperature range	Tstg	-55 to +150	°C
Maximum junction temperature	Tjmax	+150	°C

<sup>\*1</sup> Pd should not be exceeded.

● Recommended Operating Ratings (Ta=-25 to +85°C)

5 .	Symbol				
Parameter		Min.	Typ.	Max.	Unit
Power Supply Voltage	Vcc	2.7 *5	5.0	5.5	V
EN Voltage	VEN	0	-	Vcc	V
Output voltage range	Vout	1.0	-	2.5*4	V
SW average output current	Isw	-	-	2.0*5	Α

<sup>\*4</sup> In case set output voltage 1.6V or more, VccMin. = Vout +2.25V

●Electrical Characteristics (Unless otherwise specified , Ta=25°C Vcc=5V, EN=Vcc, R₁=20kΩ, R₂=7.5kΩ)

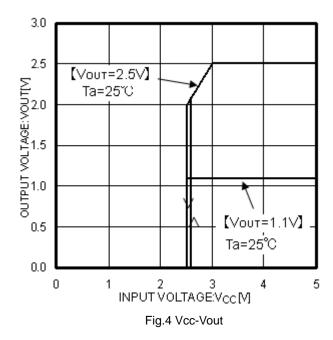
Parameter	Symbol		Limit		Unit	Conditions
raiametei	Syllibol	Min.	Тур.	Max.	Offic	Conditions
Standby Current	ISTB	-	5	20	μΑ	EN=GND
Bias Current	Icc	•	350	600	μΑ	
EN Low Voltage	VENL	-	GND	0.3	V	Stand-by Mode
EN High Voltage	VENH	2.0	Vcc	-	V	Active Mode
EN Current	IEN	-	1.25	10	μΑ	VEN=5V
Oscillation Frequency	Fosc	0.8	1	1.2	MHz	
Pch FET ON Resistance	RONP	ı	145	290	mΩ	Vcc=5V
Nch FET ON Resistance	Ronn	-	80	160	mΩ	Vcc=5V
ADJ Reference Voltage	Vadj	0.788	0.800	0.812	V	
COMP SINK Current	Icosi	10	25	-	μΑ	VADJ=1.0V
COMP Source Current	Icoso	10	25	-	μΑ	VADJ=0.6V
UVLO Threshold Voltage	Vuvlo1	2.400	2.500	2.600	V	Vcc=5V→0V
UVLO Hysteresis Voltage	Vuvlo2	2.425	2.550	2.700	V	Vcc=0V→5V
Soft Start Time	Tss	0.5	1	2	ms	
Timer Latch Time	TLATCH	1	2	4	ms	
Output Short circuit Threshold Voltage	VSCP	-	Vout × 0.5	Vout × 0.7	V	Vout=1.0V→0V

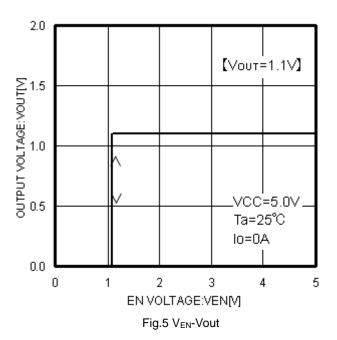
 <sup>\*2</sup> Reduced by 4.0mW for increase in Ta of 1°C above 25°C.
 \*3 Reduced by 30.0mW for increase in Ta of 1°C above 25°C

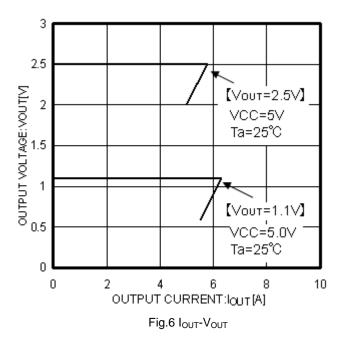
<sup>\*3</sup> Reduced by 30.0mW for increase in Ta of 1°C above 25°C. (when mounted on a board 70.0mm × 70.0mm × 1.6mm Glass-epoxy PCB)

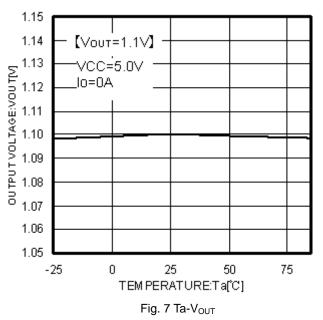
<sup>\*5</sup> Pd should not be exceeded.

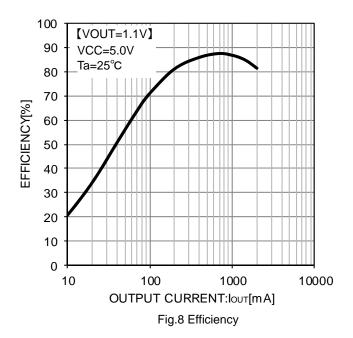
#### **●Typical Performance Curves**

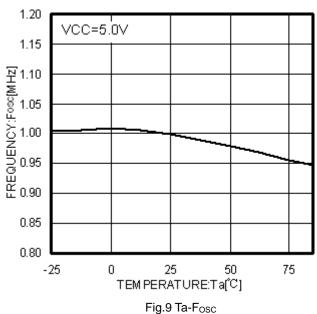


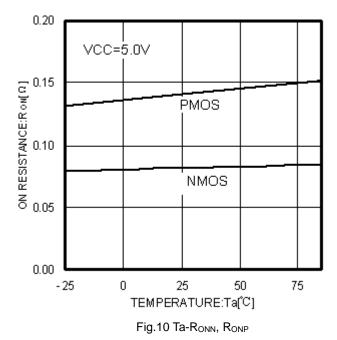


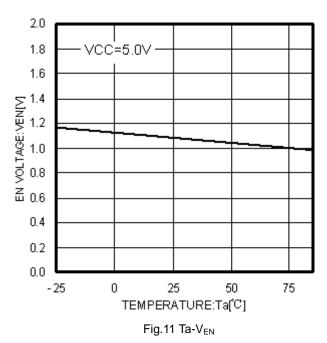


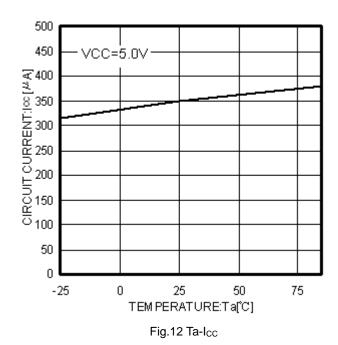












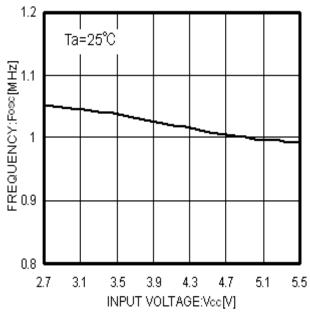


Fig.13 Vcc-Fosc

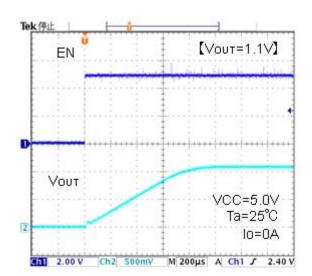


Fig.14 Soft start waveform

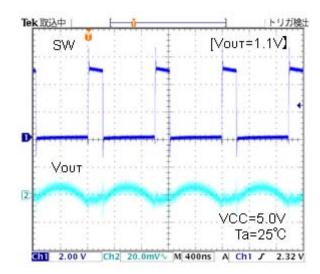


Fig.15 SW waveform Io=10mA

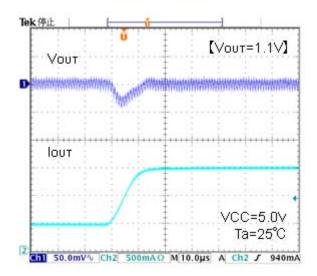


Fig. 16 Transient response Io=0.5A→1.5A(10µs)

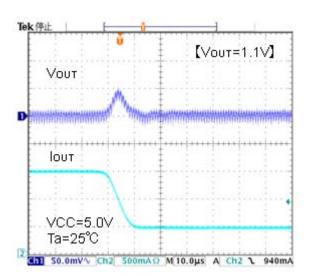


Fig. 17 Transient response Io=1.5A→0.5A(10µs)

#### **Application Information**

#### Operation

#### OSynchronous rectifier

It does not require the power to be dissipated by a rectifier externally connected to a conventional DC/DC converter IC, and its P.N junction shoot-through protection circuit limits the shoot-through current during operation, by which the power dissipation of the set is reduced.

#### OCurrent mode PWM control

Synthesizes a PWM control signal with a inductor current feedback loop added to the voltage feedback.

• PWM (Pulse Width Modulation) control

The oscillation frequency for PWM is 1 MHz. SET signal form OSC turns ON a P-channel MOS FET (while a N-channel MOS FET is turned OFF), and an inductor current  $I_L$  increases. The current comparator (Current Comp) receives two signals, a current feedback control signal (SENSE: Voltage converted from  $I_L$ ) and a voltage feedback control signal (FB), and issues a RESET signal if both input signals are identical to each other, and turns OFF the P-channel MOS FET (while a N-channel MOS FET is turned ON) for the rest of the fixed period. The PWM control repeat this operation.

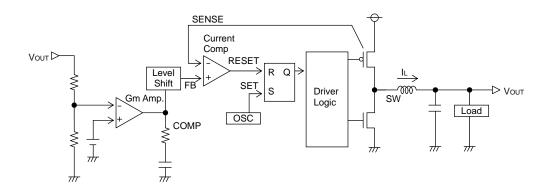


Fig.18 Diagram of current mode PWM control

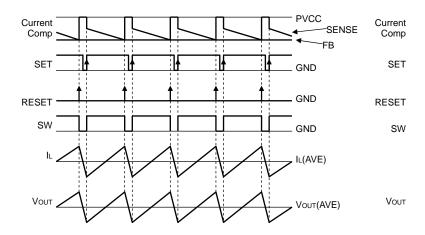


Fig.19 PWM switching timing chart

#### Description of operations

· Soft-start function

EN terminal shifted to "High" activates a soft-starter to gradually establish the output voltage with the current limited during startup, by which it is possible to prevent an overshoot of output voltage and an inrush current.

#### Shutdown function

With EN terminal shifted to "Low", the device turns to Standby Mode, and all the function blocks including reference voltage circuit, internal oscillator and drivers are turned to OFF. Circuit current during standby is 5μA (Typ.).

#### UVLO function

Detects whether the input voltage sufficient to secure the output voltage of this IC is supplied. And the hysteresis width of 50mV (Typ.) is provided to prevent output chattering.

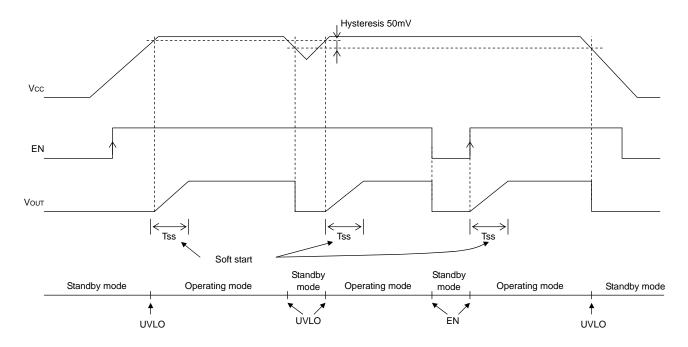


Fig.20 Soft start, Shutdown, UVLO timing chart

Short-current protection circuit with time delay function

Turns OFF the output to protect the IC from breakdown when the incorporated current limiter is activated continuously for the fixed time(TLATCH) or more. The output thus held tuned OFF may be recovered by restarting EN or by re-unlocking UVLO.

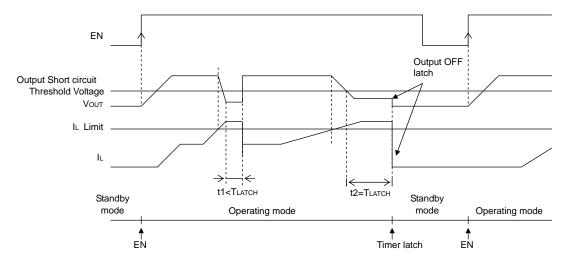
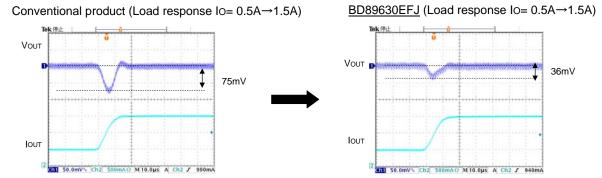


Fig.21 Short-current protection circuit with time delay timing chart

#### Information on advantages

Advantage 1: Offers fast transient response with current mode control system.



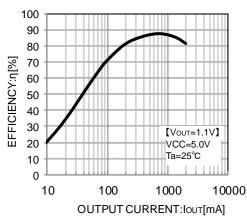
Voltage drop due to sudden change in load was reduced by about 50%.

Fig.22 Comparison of transient response

Advantage 2: Offers high efficiency with synchronous rectifier

Utilizes the synchronous rectifying mode and the low on-resistance MOS FETs incorporated as power transistor.

ON resistance of P-channel MOS FET :  $145m\Omega$  (Typ.) ON resistance of N-channel MOS FET :  $80m\Omega$  (Typ.)



Advantage 3 : • Supplied in smaller package due to small-sized power M



- Output capacitor Co required for current mode control: 10µF ceramic capacitor
- Inductance L required for the operating frequency of 1 MHz: 1.5µH inductor

Reduces a mounting area required.

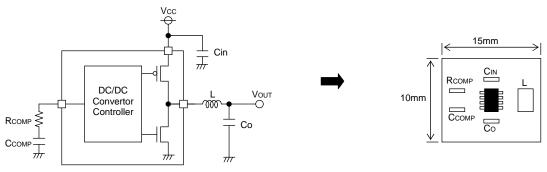


Fig.24 Example application

#### Switching regulator efficiency

Efficiency η may be expressed by the equation shown below:

$$\eta = \frac{\text{Vout} \times \text{Iout}}{\text{Vin} \times \text{lin}} \times 100[\%] = \frac{\text{Pout}}{\text{Pin}} \times 100[\%] = \frac{\text{Pout}}{\text{Pout} + \text{PD}\alpha} \times 100[\%]$$

Efficiency may be improved by reducing the switching regulator power dissipation factors  $P_D\alpha$  as follows:

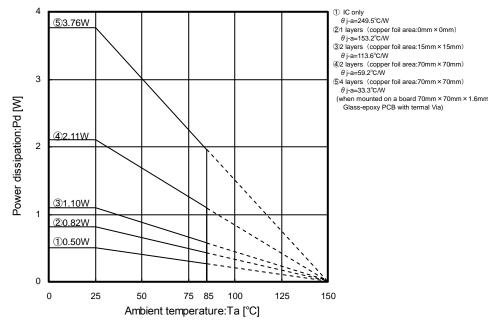
#### Dissipation factors:

- 1) ON resistance dissipation of inductor and FET: PD(I<sup>2</sup>R)
- 2) Gate charge/discharge dissipation: PD(Gate)
- 3) Switching dissipation: PD(SW)
- 4) ESR dissipation of capacitor : PD(ESR)
- 5) Operating current dissipation of IC: PD(IC)
- 1)PD( $I^2R$ )=Iou $T^2 \times$  (RcoiL+Ron) (RcoiL[ $\Omega$ ] : DC resistance of inductor, Ron[ $\Omega$ ] : ON resistance of FET, IouT[A] : Output current.)
- 2)PD(Gate)=Cgs × f ×  $V^2$  (Cgs[F]: Gate capacitance of FET, f[Hz]: Switching frequency, V[V]: Gate driving voltage of FET)
- 3)PD(SW)=  $\frac{\text{Vin}^2 \times \text{CRSS} \times \text{IOUT} \times \text{f}}{\text{IDRIVE}}$  (CRSS[F] : Reverse transfer capacitance of FET, IDRIVE[A] : Peak current of gate.)
- 4)PD(ESR)=IRMs<sup>2</sup> × ESR (IRMs[A] : Ripple current of capacitor, ESR[ $\Omega$ ] : Equivalent series resistance.)
- 5)PD(IC)=Vin × Icc (Icc[A] : Circuit current.)

#### Consideration on permissible dissipation and heat generation

As this IC functions with high efficiency without significant heat generation in most applications, no special consideration is needed on permissible dissipation or heat generation. In case of extreme conditions, however, including lower input voltage, higher output voltage, heavier load, and/or higher temperature, the permissible dissipation and/or heat generation must be carefully considered.

For dissipation, only conduction losses due to DC resistance of inductor and ON resistance of FET are considered. Because the conduction losses are considered to play the leading role among other dissipation mentioned above including gate charge/discharge dissipation and switching dissipation.



P=IOLIT<sup>2</sup> x RON RON=D × RONP+(1-D)RONN

D : ON duty (=VOUT/VCC)

RCOIL : DC resistance of coil
RONP : ON resistance of P-channel MOS FET RONN: ON resistance of N-channel MOS FET

IOUT : Output current

Fig.25 Thermal derating curve (HTSOP-J8)

Ex.)Vcc=5V, Vout=1.1V, Ronp=0.145  $\Omega$  , Ronn=0.08  $\Omega$ IOUT=2A, for example, D=Vout/Vcc=1.1/5=0.22  $Ron=0.22 \times 0.145 + (1-0.22) \times 0.08$ =0.0319+0.0624  $=0.0943[\Omega]$ 

 $P=2^2 \times 0.0943 = 0.3772[W]$ 

As RONP is greater than RONN in this IC, the dissipation increases as the ON duty becomes greater. With the consideration on the dissipation as above, thermal design must be carried out with sufficient margin allowed.

#### Selection of components externally connected

#### 1. Selection of inductor (L)

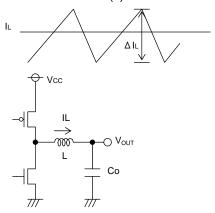


Fig.26 Output ripple current

The inductance significantly depends on output ripple current. As seen in the equation (1), the ripple current decreases as the inductor and/or switching frequency increases.

$$\Delta \, \mathsf{IL} = \frac{(\mathsf{VCC}\text{-}\mathsf{VOUT}) \times \mathsf{VOUT}}{\mathsf{L} \times \mathsf{VCC} \times \mathsf{f}} \, [\mathsf{A}] \cdot \cdot \cdot (\mathsf{1})$$

Appropriate ripple current at output should be 20% more or less of the maximum output current.

$$\Delta$$
 IL=0.2 × IOUTmax. [A] · · · (2)

$$L = \frac{(\text{Vcc-Vout}) \times \text{Vout}}{\Delta \text{ IL} \times \text{Vcc} \times \text{f}} [\text{H}] \cdot \cdot \cdot (3)$$
 (\Delta \text{IL: Output ripple current, and f: Switching frequency)}

\*Current exceeding the current rating of the inductor results in magnetic saturation of the inductor, which decreases efficiency. The inductor must be selected allowing sufficient margin with which the peak current may not exceed its current rating.

If Vcc=5V, Vout=1.1V, f=1MHz,  $\Delta$  IL=0.2 × 2A=0.4A, for example, (BD89630EFJ)

$$L = \frac{(5-1.1) \times 1.1}{0.4 \times 5 \times 1M} = 2.1 \mu \rightarrow 2.2 [\mu H]$$

\*Select the inductor of low resistance component (such as DCR and ACR) to minimize dissipation in the inductor for better efficiency.

#### 2. Selection of output capacitor (Co)

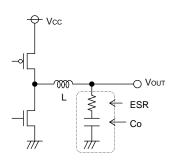


Fig.27 Output capacitor

Output capacitor should be selected with the consideration on the stability region and the equivalent series resistance required to smooth ripple voltage.

Output ripple voltage is determined by the equation (4):

$$\triangle$$
 Vout= $\triangle$  IL × ESR [V] · · · (4)

(Δ IL: Output ripple current, ESR: Equivalent series resistance of output capacitor)

\*Rating of the capacitor should be determined allowing sufficient margin against output voltage. A 10µF to 100µF ceramic capacitor is recommended. Less ESR allows reduction in output ripple voltage.

#### 3. Selection of input capacitor (Cin)

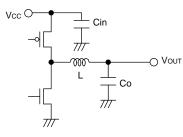


Fig.28 Input capacitor

Input capacitor to select must be a low ESR capacitor of the capacitance sufficient to cope with high ripple current to prevent high transient voltage. The ripple current IRMS is given by the equation (5):

IRMS=IOUT × 
$$\frac{\sqrt{\text{VOUT}(\text{VCC-VOUT})}}{\text{VCC}}$$
 [A] · · · (5)

< Worst case > IRMS(max.)

When Vcc is twice the 
$$V_{OUT}$$
, IRMS=  $\frac{IOUT}{2}$ 

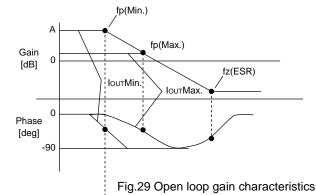
If Vcc=5V, Vout=1.1V, and Ioutmax.= 2A, (BD89630EFJ)

IRMS=2 × 
$$\frac{\sqrt{1.1 \times (5-1.1)}}{5}$$
 = 0.828[ARMS]

A low ESR 22µF/10V ceramic capacitor is recommended to reduce ESR dissipation of input capacitor for better efficiency.

#### 4. Determination of RCOMP, CCOMP that works as a phase compensator

As the Current Mode Control is designed to limit a inductor current, a pole (phase lag) appears in the low frequency area due to a CR filter consisting of a output capacitor and a load resistance, while a zero (phase lead) appears in the high frequency area due to the output capacitor and its ESR. So, the phases are easily compensated by adding a zero to the power amplifier output with C and R as described below to cancel a pole at the power amplifier.



$$fp = \frac{1}{2\pi \times Ro \times Co}$$

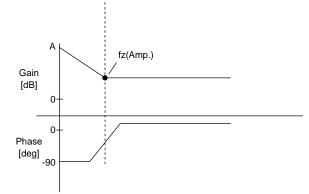
$$fz(ESR) = \frac{1}{2\pi \times ESR \times Co}$$

#### Pole at power amplifier

When the output current decreases, the load resistance Ro increases and the pole frequency lowers.

$$fp(Min.) = \frac{1}{2\pi \times RoMax. \times Co} [Hz] \leftarrow with lighter load$$

$$fp(\text{Max.}) = \frac{1}{2\pi \times \text{RoMin.} \times \text{Co}} \quad [\text{Hz}] \leftarrow \text{with heavier load}$$



#### Zero at power amplifier

Increasing capacitance of the output capacitor lowers the pole frequency while the zero frequency does not change. (This is because when the capacitance is doubled, the capacitor ESR reduces to half.)

$$fz(Amp.) = \frac{1}{2\pi \times RITH \times CITH}$$

Fig.30 Error amp phase compensation characteristics

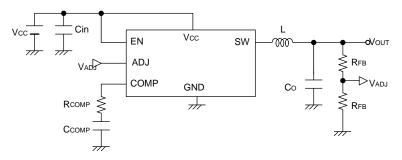


Fig.31 Typical application

Stable feedback loop may be achieved by canceling the pole fp (Min.) produced by the output capacitor and the load resistance with CR zero correction by the error amplifier.

$$fz(Amp.) = fp(Min.)$$

$$\frac{1}{2\pi \times RCOMP \times CCOMP} = \frac{1}{2\pi \times ROMax. \times CO}$$

#### 5. Determination of output voltage

The output voltage VouT is determined by the equation (6): VouT=(R2/R1+1) × VADJ · · · (6) VADJ: Voltage at ADJ terminal (0.8V Typ.) With R1 and R2 adjusted, the output voltage may be determined as required.

Adjustable output voltage range : 1.0V to 2.5V

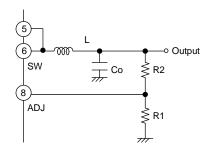


Fig.32 Determination of output voltage

Use 1 k $\Omega$  to 100 k $\Omega$  resistor for R1. If a resistor of the resistance higher than 100 k $\Omega$  is used, check the assembled set carefully for ripple voltage etc.

The lower limit of input voltage depends on the output voltage. Basically, it is recommended to use in the condition :

VCCmin = VOUT+2.25V.

Fig.33. shows the necessary output current value at the lower limit of input voltage. (DCR of inductor :  $0.05\,\Omega)$ 

This data is the characteristic value, so it' doesn't guarantee the operation range,

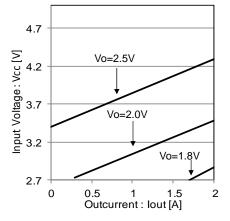


Fig.33 minimum input voltage in each output voltage

#### ● Cautions on PC Board layout

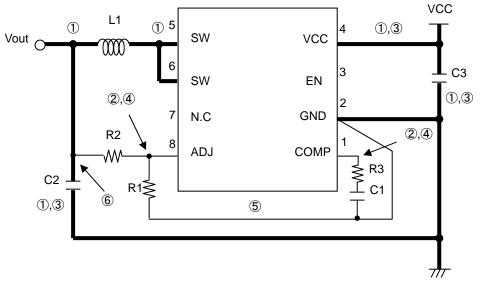
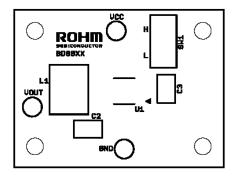


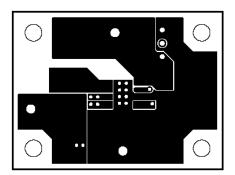
Fig.34 Layout diagram

- ①To avoid conduction loss, please keep Black thick line as short and thick as possible.
- ②Don't close to switching current loop.
- 3 Close to IC pin as possible.
- 4 Keep PCB trace as short as possible.
- ⑤Use single point ground structure to connect with Pin2.
- 6Close to C2 as possible.
  - HTSOP-J8 (BD89630EFJ) has thermal PAD on the reverse of the package.

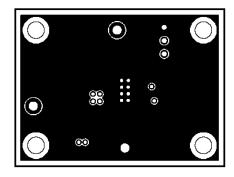
    The package thermal performance may be enhanced by bonding the PAD to GND plane which take a large area of PCB.



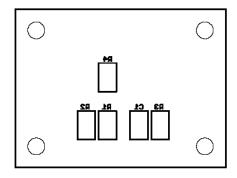
Top Silkscreen Overlay



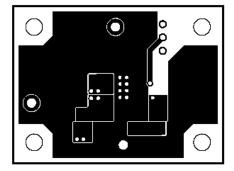
Top Layer



Middle Layer



Bottom Silkscreen Overlay



Bottom Layer

Fig.35 Reference PCB Layout Pattern

●Recommended components Lists on above application

Symbol	Part	Value		Manufacturer	Series
L	Coil	1.5µH		TDK	VLC6045T-1R5N
CIN	Ceramic capacitor	Vcc-VOUT>3V	10μF	Kyocera	CM316X5R106M10A
CIN		Vcc-VOUT<3V	22µF	Kyocera	CM32X5R226M10A
CO	Ceramic capacitor	10μ	F	Kyocera	CM316X5R106M10A
		VOUT=1.0V	330pF	Murata	GRM18 Series
	Ceramic capacitor	VOUT=1.1V	330pF	Murata	GRM18 Series
ССОМР		VOUT=1.2V	330pF	Murata	GRM18 Series
CCOIVIP		VOUT=1.5V	390pF	Murata	GRM18 Series
		VOUT=1.8V	390pF	Murata	GRM18 Series
		VOUT=2.5V	390pF	Murata	GRM18 Series
		VOUT=1.0V	2kΩ	Rohm	MCR03 Series
	Resistance	VOUT=1.1V	2kΩ	Rohm	MCR03 Series
RCOMP		VOUT=1.2V	$2.4k\Omega$	Rohm	MCR03 Series
RCOIVIP		VOUT=1.5V	$2.4k\Omega$	Rohm	MCR03 Series
		VOUT=1.8V	3.6kΩ	Rohm	MCR03 Series
		VOUT=2.5V	5.6k Ω	Rohm	MCR03 Series

<sup>\*</sup> The parts list presented above is an example of recommended parts. Although the parts are sound, actual circuit characteristics should be checked on your application carefully before use. Be sure to allow sufficient margins to accommodate variations between external devices and this IC when employing the depicted circuit with other circuit constants modified. Both static and transient characteristics should be considered in establishing these margins.

#### ●I/O equivalence circuit

[BD89630EFJ]

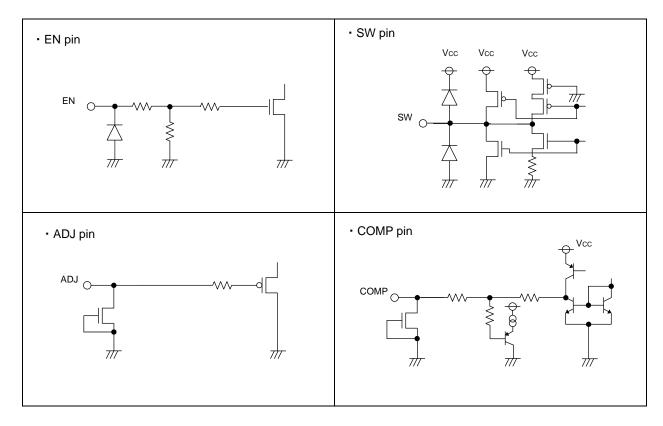


Fig.36 I/O equivalence circuit

#### Operational Notes

#### 1. Absolute Maximum Ratings

While utmost care is taken to quality control of this product, any application that may exceed some of the absolute maximum ratings including the voltage applied and the operating temperature range may result in breakage. If broken, short-mode or open-mode may not be identified. So if it is expected to encounter with special mode that may exceed the absolute maximum ratings, it is requested to take necessary safety measures physically including insertion of fuses.

#### 2. Electrical potential at GND

GND must be designed to have the lowest electrical potential In any operating conditions.

#### 3. Short-circuiting between terminals, and mismounting

When mounting to pc board, care must be taken to avoid mistake in its orientation and alignment. Failure to do so may result in IC breakdown. Short-circuiting due to foreign matters entered between output terminals, or between output and power supply or GND may also cause breakdown.

#### 4. Operation in Strong electromagnetic field

Be noted that using the IC in the strong electromagnetic radiation can cause operation failures.

#### 5. Thermal shutdown protection circuit

Thermal shutdown protection circuit is the circuit designed to isolate the IC from thermal runaway, and not intended to protect and guarantee the IC. So, the IC the thermal shutdown protection circuit of which is once activated should not be used thereafter for any operation originally intended.

#### 6. Inspection with the IC set to a pc board

If a capacitor must be connected to the pin of lower impedance during inspection with the IC set to a pc board, the capacitor must be discharged after each process to avoid stress to the IC. For electrostatic protection, provide proper grounding to assembling processes with special care taken in handling and storage. When connecting to jigs in the inspection process, be sure to turn OFF the power supply before it is connected and removed.

#### 7. Input to IC terminals

This is a monolithic IC with  $P^+$  isolation between P-substrate and each element as illustrated below. This P-layer and the N-layer of each element form a P-N junction, and various parasitic element are formed. If a resistor is joined to a transistor terminal as shown in Fig 37.

OP-N junction works as a parasitic diode if the following relationship is satisfied;

GND>Terminal A (at resistor side), or GND>Terminal B (at transistor side); and

Oif GND>Terminal B (at NPN transistor side),

a parasitic NPN transistor is activated by N-layer of other element adjacent to the above-mentioned parasitic diode.

The structure of the IC inevitably forms parasitic elements, the activation of which may cause interference among circuits, and/or malfunctions contributing to breakdown. It is therefore requested to take care not to use the device in such manner that the voltage lower than GND (at P-substrate) may be applied to the input terminal, which may result in activation of parasitic elements.

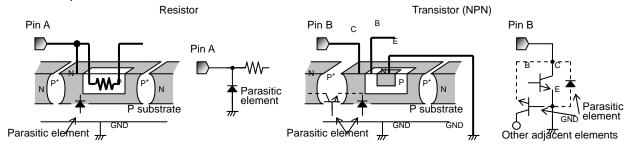


Fig.37 Simplified structure of monorisic IC

#### 8. Ground wiring pattern

If small-signal GND and large-current GND are provided, It will be recommended to separate the large-current GND pattern from the small-signal GND pattern and establish a single ground at the reference point of the set PCB so that resistance to the wiring pattern and voltage fluctuations due to a large current will cause no fluctuations in voltages of the small-signal GND. Pay attention not to cause fluctuations in the GND wiring pattern of external parts as well.

#### 9. Selection of inductor

It is recommended to use an inductor with a series resistance element (DCR)  $0.1\,\Omega$  or less. Especially, in case output voltage is set 1.6V or more, note that use of a high DCR inductor will cause an inductor loss, resulting in decreased output voltage. Should this condition continue for a specified period (soft start time + timer latch time), output short circuit protection will be activated and output will be latched OFF. When using an inductor over  $0.1\,\Omega$ , be careful to ensure adequate margins for variation between external devices and this IC, including transient as well as static characteristics. Furthermore, in any case, it is recommended to start up the output with EN after supply voltage is within operation range.

#### Status of this document

The Japanese version of this document is formal specification. A customer may use this translation version only for a reference to help reading the formal version.

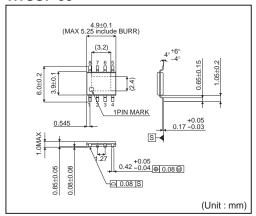
If there are any differences in translation version of this document formal version takes priority

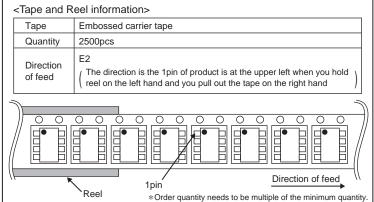
#### Ordering Information



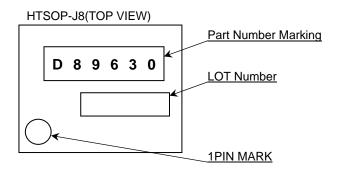
#### ● Physical Dimension Tape and Reel Information

#### HTSOP-J8





#### Marking Diagram



Revision History

Date	Revision	Changes
28.Aug.2012	001	New Release

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JAPAN	USA	EU	CHINA	
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CLASSIV	CLASSIII	CLASSⅢ	CLASSIII	

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  - [h] Use of the Products in places subject to dew condensation
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  - [d] the Products are exposed to high Electrostatic
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- Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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